Silicon Phototransistor

FEATURES

- Side-looking plastic package
- 18° (nominal) acceptance angle
- Enhanced coupling distance
- · Internal visible light rejection filter
- · Low profile for design flexibility
- Wide sensitivity ranges
- Mechanically matched to SEP8736 infrared emitting diode



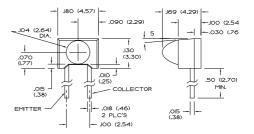
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DESCRIPTION

The SDP8436 is an NPN silicon phototransistor molded in a black plastic package which combines the mounting advantages of a side-looking package with the narrow acceptance angle and high optical gain of a T-1 package. The SDP8436 is designed for those applications which require longer coupling distances than standard side-looking devices can provide, such as touch screens. The device is also well suited to applications in which adjacent channel crosstalk could be a problem. The package is highly transmissive to the IR source energy while it provides effective shielding against visible ambient light.

OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals ±0.005(0.12) 2 plc decimals ±0.020(0.51)



DIM_019.ds4



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ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Light Current	lL				mA	V _{CE} =5 V
SDP8436-001		0.50				H=1 mW/cm ^{2 (1)}
SDP8436-002		4.00		10.0		
SDP8436-003		7.00		17.5		
SDP8436-004		12.5				
Collector Dark Current	Iceo			100	nA	V _{CE} =15 V, H=0
Collector-Emitter Breakdown Voltage	V _(BR) CEO	30			V	Ic=100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector-Emitter Saturation Voltage	VCE(SAT)			0.4	V	Ic=0.1 mA
						H=1 mW/cm ²
Angular Response (2)	Ø		18		degr.	I _F =Constant
Rise And Fall Time	t _r , t _f		15		μs	Vcc=5 V, I _L =1 mA
						R _L =1000 Ω

Notes

- 1. The radiation source is an IRED with a peak wavelength of 880 nm.
 2. Angular response is defined as the total included angle between the half sensitivity points.

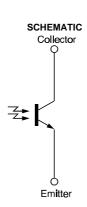
ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted) Collector-Emitter Voltage 30 V Emitter-Collector Voltage 5 V Power Dissipation 100 mW (1) -40°C to 85°C Operating Temperature Range Storage Temperature Range -40°C to 85°C Soldering Temperature (5 sec) 240°C

Notes

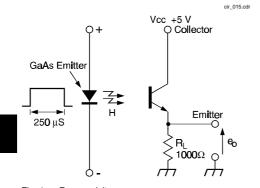
1. Derate linearly from 25°C free-air temperature at the rate of

0.78 mW/°C.

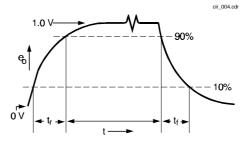


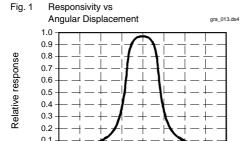
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SWITCHING TIME TEST CIRCUIT



SWITCHING WAVEFORM





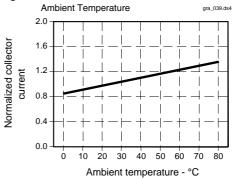
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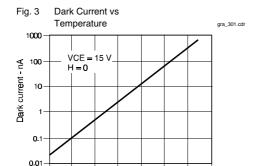
Angular displacement - degrees

+10 +20 +30 +40

-30 -20 -10

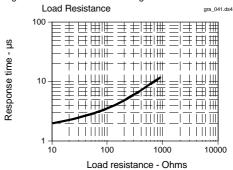
Fig. 2 Collector Current vs





Free-air temperature - °C

Fig. 4 Non-Saturated Switching Time vs

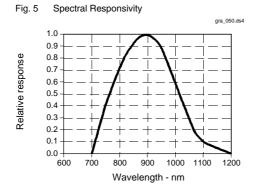


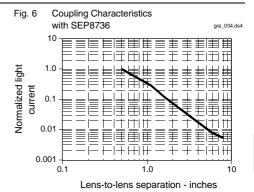
Honeywell

Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

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